



BUK7Y25-80E

N-channel 80 V, 25 mΩ standard level MOSFET in LPAK56

20 February 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in an LPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with $V_{GS(th)}$ rating of greater than 1 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C};$ Fig. 1	-	-	39	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ Fig. 2	-	-	95	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; T_j = 25\text{ °C};$ Fig. 11	-	16.7	25	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 10\text{ A}; V_{DS} = 64\text{ V};$ $T_j = 25\text{ °C};$ Fig. 13 ; Fig. 14	-	8.2	-	nC

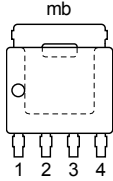
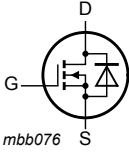


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK; Power-SO8 (SOT669)</p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y25-80E	LPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y25-80E	72580E

8. Limiting values

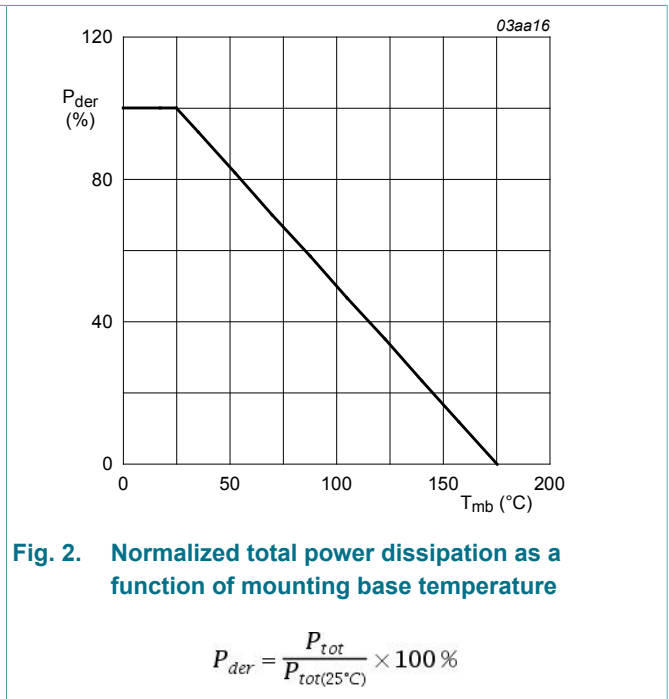
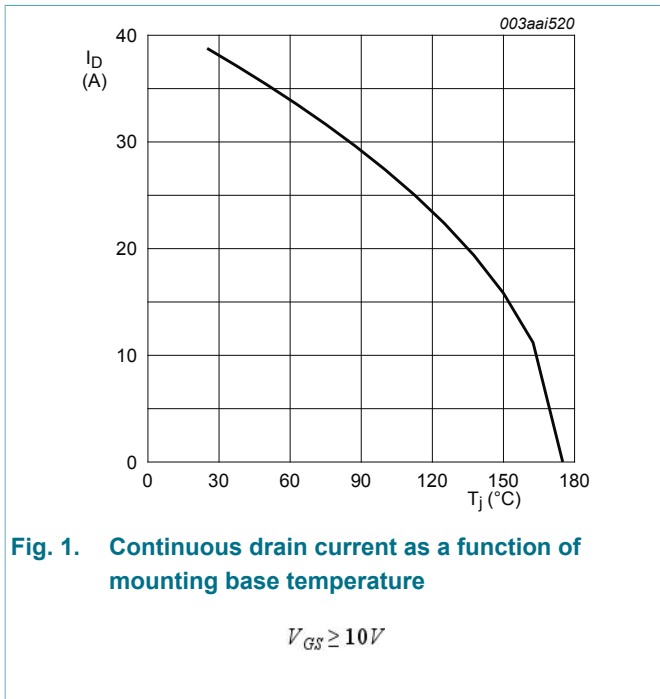
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	80	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	80	V
V_{GS}	gate-source voltage	$T_j \leq 175\text{ °C}; DC$	-20	20	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V}; \text{Fig. 1}$	-	39	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V}; \text{Fig. 1}$	-	27.5	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}; \text{pulsed}; t_p \leq 10\text{ }\mu\text{s}; \text{Fig. 4}$	-	156	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	95	W
T_{stg}	storage temperature		-55	175	°C

Symbol	Parameter	Conditions	Min	Max	Unit
T _j	junction temperature		-55	175	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	39	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	156	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 39 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; Fig. 3	[1][2]	-	43.6 mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.



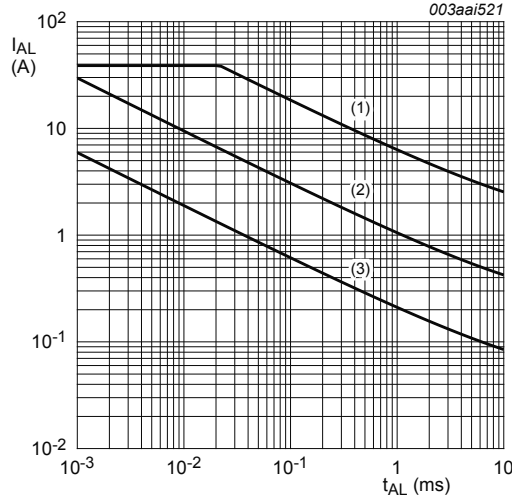


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j (int)} = 25^{\circ}C$; (2) $T_{j (int)} = 150^{\circ}C$; (3) Repetitive Avalanche

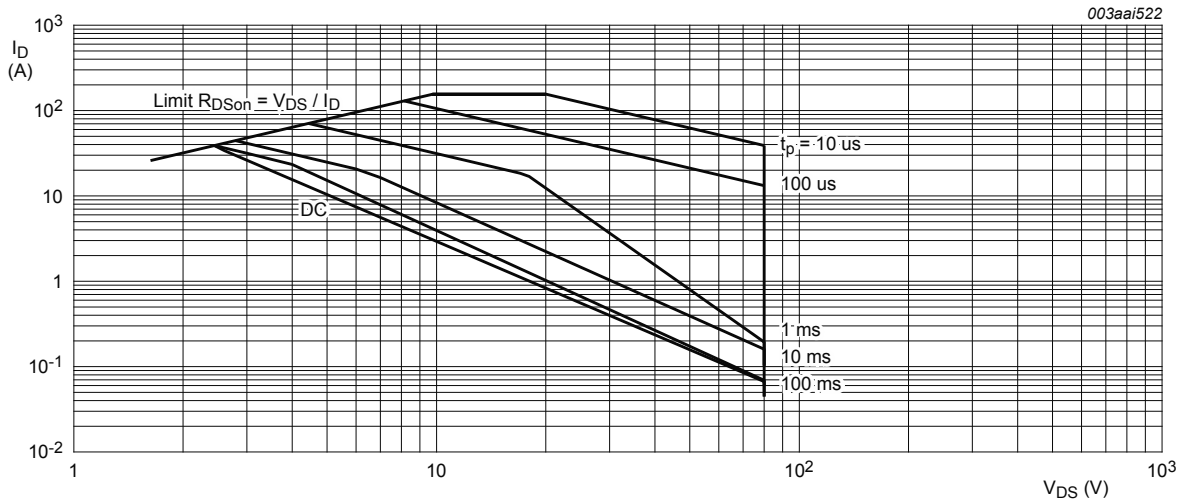


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	1.58	K/W

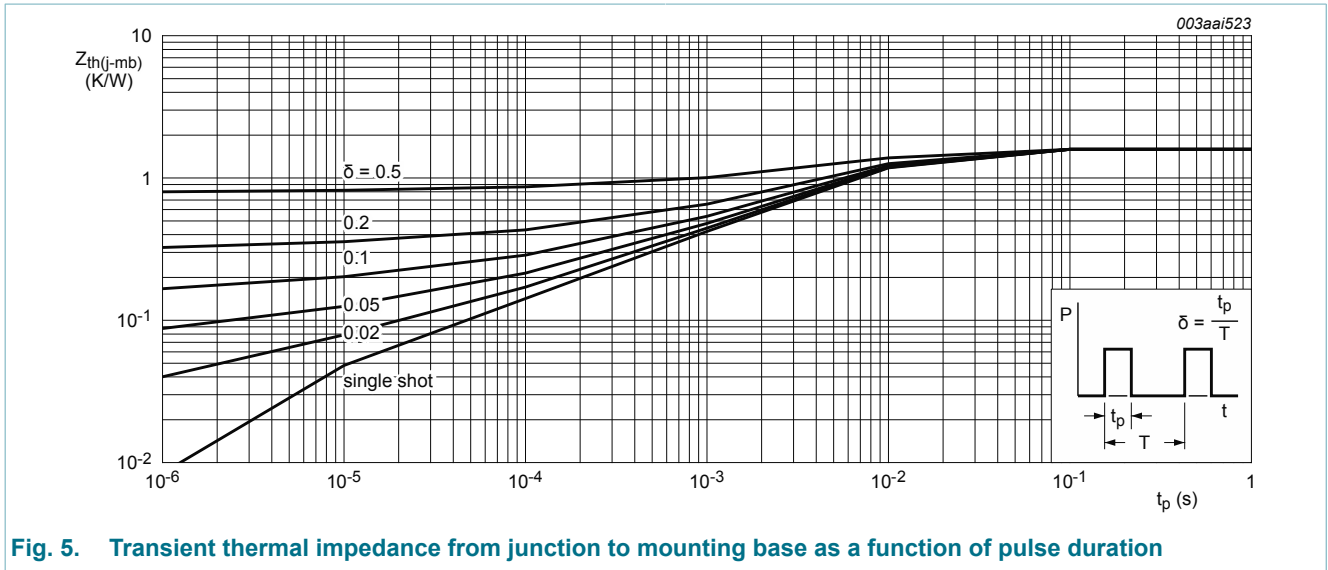


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

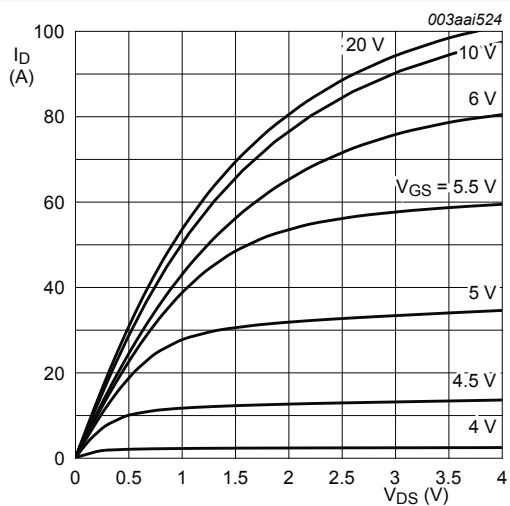
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	80	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C;$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ C;$ Fig. 9	-	-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ C;$ Fig. 9	1	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.02	1	μA
		$V_{DS} = 80 V; V_{GS} = 0 V; T_j = 175 \text{ }^\circ C$	-	-	500	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 10 A; T_j = 25 \text{ }^\circ C;$ Fig. 11	-	16.7	25	mΩ
		$V_{GS} = 10 V; I_D = 10 A; T_j = 175 \text{ }^\circ C;$ Fig. 12; Fig. 11	-	-	62.75	mΩ
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 10 A; V_{DS} = 64 V; V_{GS} = 10 V;$ $T_j = 25 \text{ }^\circ C;$ Fig. 13; Fig. 14	-	25.9	-	nC
Q_{GS}	gate-source charge		-	5.9	-	nC
Q_{GD}	gate-drain charge		-	8.2	-	nC

N-channel 80 V, 25 mΩ standard level MOSFET in LPAK56

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz};$	-	1364	1800	pF
C_{oss}	output capacitance	$T_j = 25\text{ }^\circ\text{C};$ Fig. 15	-	150	180	pF
C_{rss}	reverse transfer capacitance		-	92	127	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 60\text{ V}; R_L = 5\text{ }^\Omega; V_{GS} = 10\text{ V};$	-	6.9	-	ns
t_r	rise time	$R_{G(ext)} = 5\text{ }^\Omega; T_j = 25\text{ }^\circ\text{C}$	-	9.2	-	ns
$t_{d(off)}$	turn-off delay time		-	17.5	-	ns
t_f	fall time		-	10.5	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 10\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ Fig. 16	-	0.82	1.2	V
t_{rr}	reverse recovery time	$I_S = 10\text{ A}; di_S/dt = -100\text{ A}/\mu\text{s}; V_{GS} = 0\text{ V};$	-	25.4	-	ns
Q_r	recovered charge	$V_{DS} = 25\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	30.7	-	nC



$T_j = 25\text{ }^\circ\text{C}; t_p = 300\text{ }^\mu\text{s}$

Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

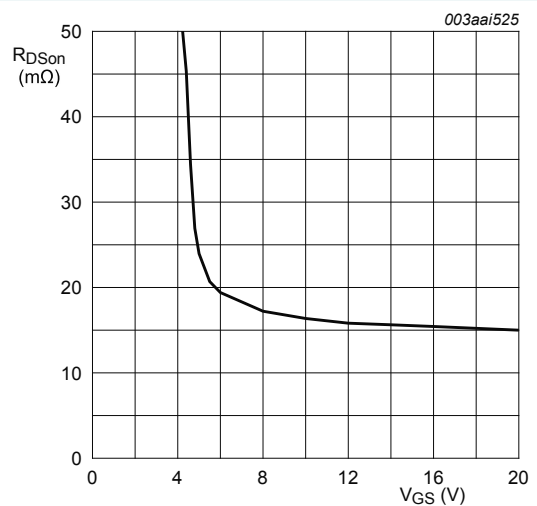


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^\circ\text{C}; I_D = 10\text{ A}$

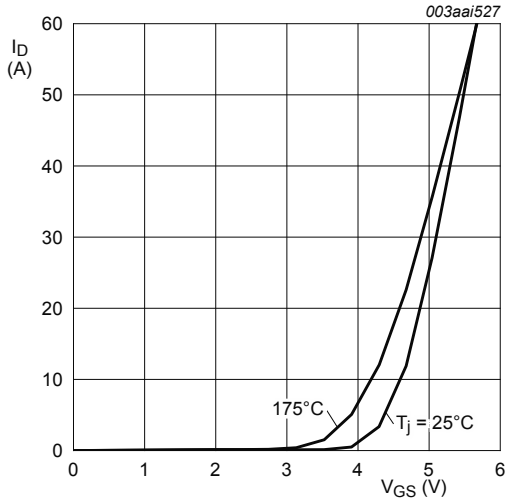


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10V$



Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

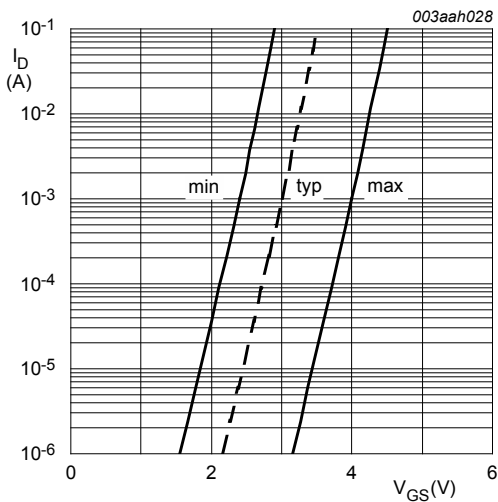


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^\circ C; V_{DS} = 5V$

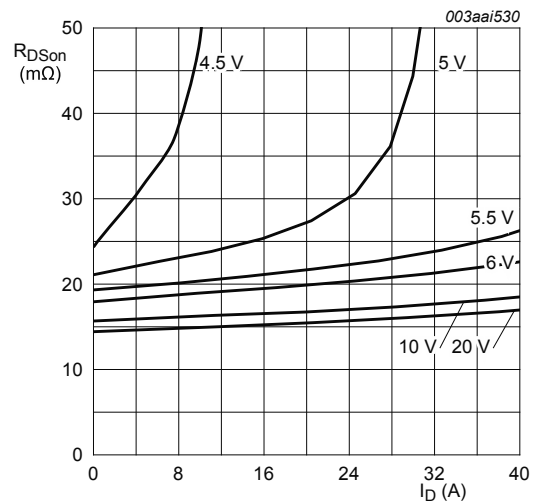


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^\circ C; t_p = 300 \mu s$

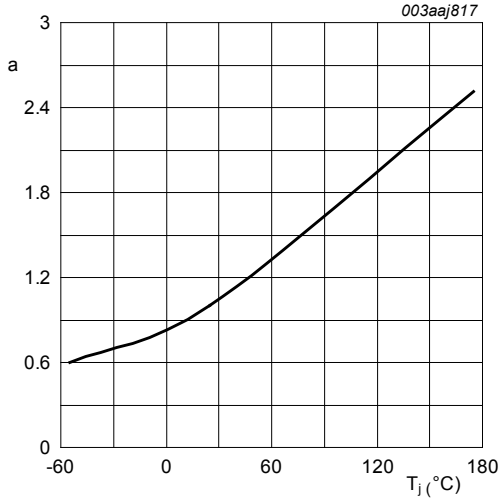


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)(25^\circ C)}}$$



Fig. 13. Gate charge waveform definitions

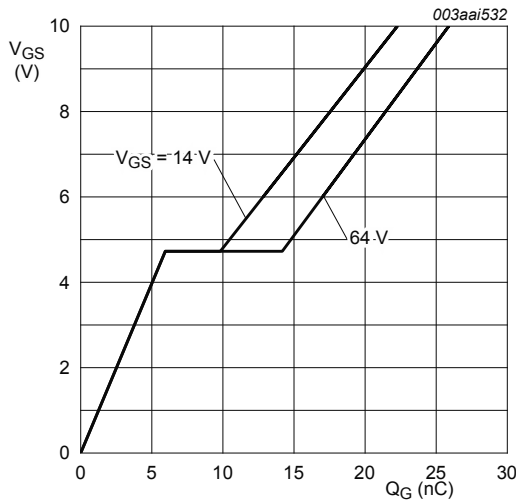


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ C; I_D = 10A$$

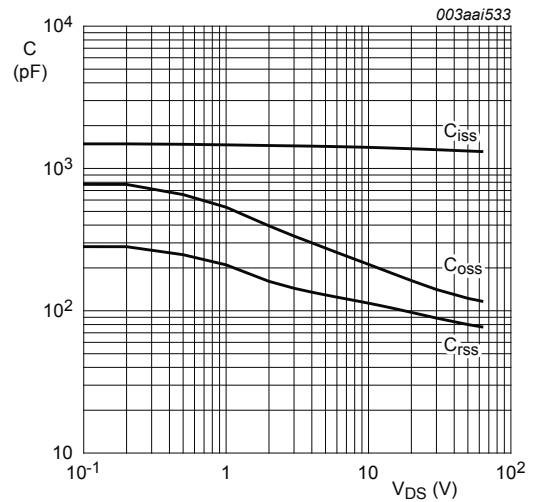


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

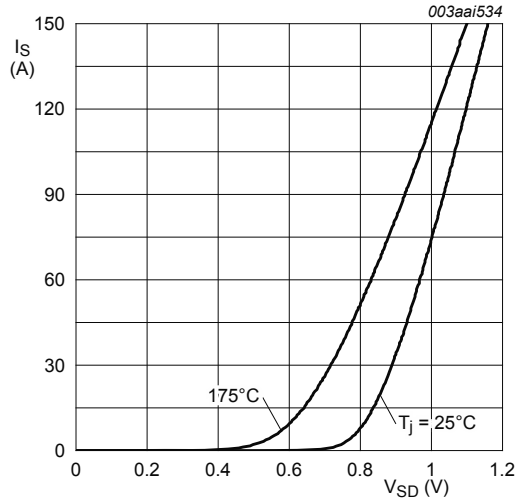


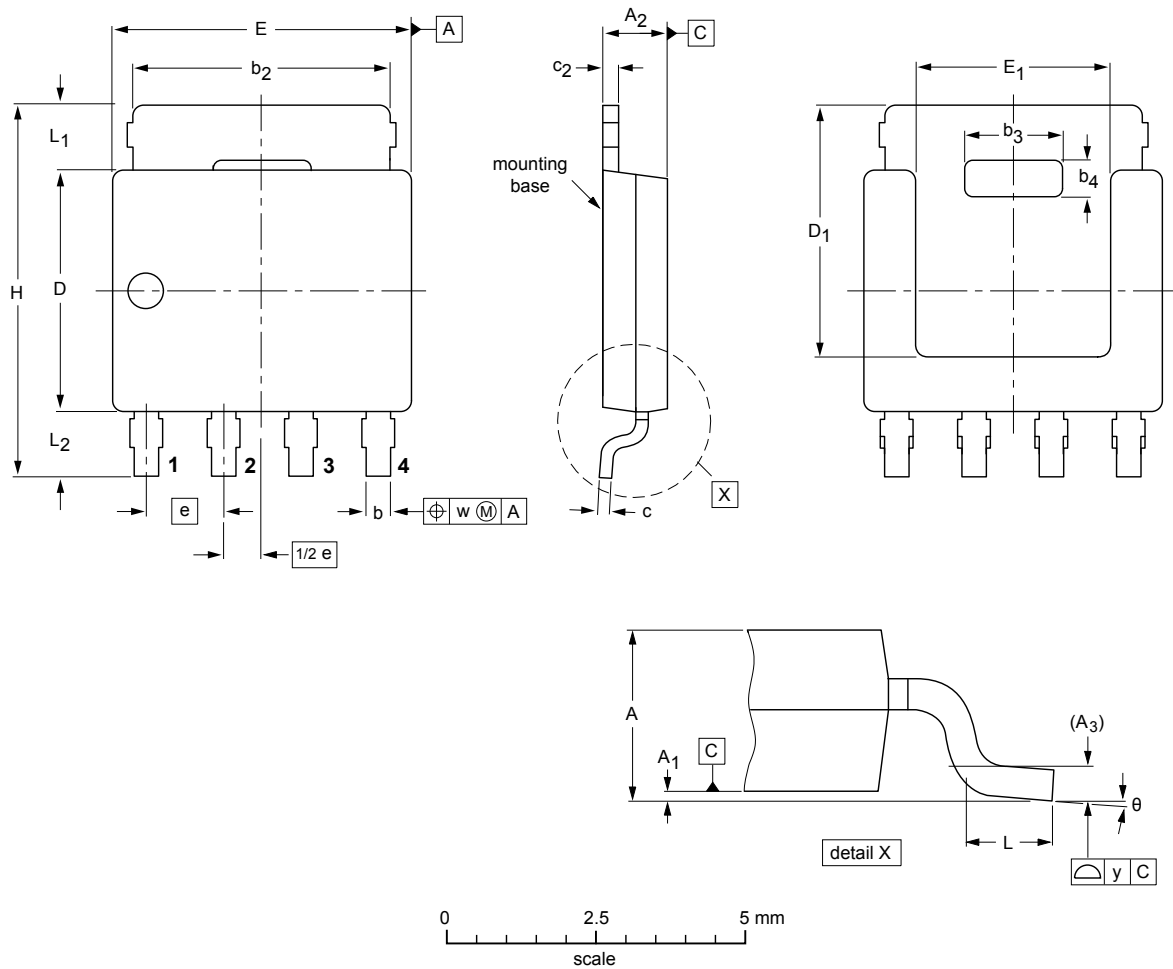
Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline

Plastic single-ended surface-mounted package (LPAK; Power-SO8); 4 leads

SOT669



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	A ₂	A ₃	b	b ₂	b ₃	b ₄	c	c ₂	D ⁽¹⁾	D ₁ ⁽¹⁾ max	E ⁽¹⁾	E ₁ ⁽¹⁾	e	H	L	L ₁	L ₂	w	y	θ
mm	1.20 1.01	0.15 0.00	1.10 0.95	0.25	0.50 0.35	4.41 3.62	2.2 2.0	0.9 0.7	0.25 0.19	0.30 0.24	4.10 3.80	4.20	5.0 4.8	3.3 3.1	1.27	6.2 5.8	0.85 0.40	1.3 0.8	1.3 0.8	0.25	0.1	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT669		MO-235				06-03-16 11-03-25

Fig. 17. Package outline LPAK; Power-SO8 (SOT669)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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